

SEMiX101GD12E4s



SEMiX[®] 13

Trench IGBT Modules

SEMiX101GD12E4s

Features

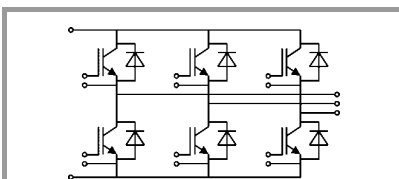
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- UL recognized, file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperature limited to $T_C=125^{\circ}C$ max.
- Product reliability results are valid for $T_J=150^{\circ}C$



GD

Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
IGBT				
V_{CES}			1200	V
I_C	$T_J = 175^{\circ}C$	$T_C = 25^{\circ}C$	160	A
		$T_C = 80^{\circ}C$	123	A
I_{Cnom}			100	A
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$		300	A
V_{GES}			-20 ... 20	V
t_{psc}	$V_{CC} = 800 V$ $V_{GE} \leq 20 V$ $V_{CES} \leq 1200 V$	$T_J = 150^{\circ}C$	10	μs
T_J			-40 ... 175	$^{\circ}C$
Inverse diode				
I_F	$T_J = 175^{\circ}C$	$T_C = 25^{\circ}C$	121	A
		$T_C = 80^{\circ}C$	91	A
I_{Fnom}			100	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$		300	A
I_{FSM}	$t_p = 10 ms, \sin 180^{\circ}, T_J = 25^{\circ}C$		550	A
T_J			-40 ... 175	$^{\circ}C$
Module				
$I_{t(RMS)}$			600	A
T_{stg}			-40 ... 125	$^{\circ}C$
V_{isol}	AC sinus 50Hz, t = 1 min		4000	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
$V_{CE(sat)}$	$I_C = 100 A$ $V_{GE} = 15 V$ chipllevel	$T_J = 25^{\circ}C$		1.8	2.05	V
		$T_J = 150^{\circ}C$		2.2	2.4	V
V_{CE0}				0.8	0.9	V
				0.7	0.8	V
r_{CE}	$V_{GE} = 15 V$	$T_J = 25^{\circ}C$		10.0	11.5	$m\Omega$
		$T_J = 150^{\circ}C$		15.0	16.0	$m\Omega$
$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C = 3.8 mA$		5	5.8	6.5	V
I_{CES}	$V_{GE} = 0 V$ $V_{CE} = 1200 V$	$T_J = 25^{\circ}C$		0.1	0.3	mA
		$T_J = 150^{\circ}C$				mA
C_{ies}				6.2		nF
C_{oes}	$V_{CE} = 25 V$ $V_{GE} = 0 V$			0.41		nF
C_{res}				0.34		nF
Q_G	$V_{GE} = -8 V \dots +15 V$			565		nC
R_{Gint}	$T_J = 25^{\circ}C$			7.50		Ω
$t_{d(on)}$	$V_{CC} = 600 V$	$T_J = 150^{\circ}C$		187		ns
t_r	$I_C = 100 A$	$T_J = 150^{\circ}C$		35		ns
E_{on}	$R_{G on} = 1 \Omega$	$T_J = 150^{\circ}C$		10.8		mJ
$t_{d(off)}$	$R_{G off} = 1 \Omega$	$T_J = 150^{\circ}C$		467		ns
t_f	$di/dt_{on} = 3100 A/\mu s$ $di/dt_{off} = 1200 A/\mu s$	$T_J = 150^{\circ}C$		94		ns
E_{off}	$T_J = 150^{\circ}C$			13.3		mJ
$R_{th(j-c)}$	per IGBT				0.27	K/W

SEMiX101GD12E4s



SEMiX[®] 13

Trench IGBT Modules

SEMiX101GD12E4s

Features

- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- UL recognized, file no. E63532

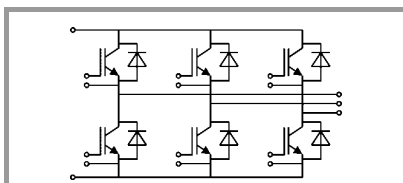
Typical Applications*

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperature limited to $T_C=125^\circ\text{C}$ max.
- Product reliability results are valid for $T_j=150^\circ\text{C}$

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
$V_F = V_{EC}$	$I_F = 100\text{ A}$	$T_j = 25^\circ\text{C}$		2.2	2.52	V
	$V_{GE} = 0\text{ V}$	$T_j = 150^\circ\text{C}$		2.1	2.5	V
	chip					
V_{F0}		$T_j = 25^\circ\text{C}$	1.1	1.3	1.5	V
		$T_j = 150^\circ\text{C}$	0.7	0.9	1.1	V
r_F		$T_j = 25^\circ\text{C}$	8.0	9.0	10.2	m Ω
		$T_j = 150^\circ\text{C}$	10.5	12.5	13.7	m Ω
I_{RRM}	$I_F = 100\text{ A}$	$T_j = 150^\circ\text{C}$		95		A
Q_{rr}	$di/dt_{off} = 3000\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		16		μC
E_{rr}	$V_{GE} = -15\text{ V}$	$T_j = 150^\circ\text{C}$		6.5		mJ
	$V_{CC} = 600\text{ V}$					
$R_{th(j-c)}$	per diode				0.48	K/W
Module						
L_{CE}				20		nH
R_{CC+EE}	res., terminal-chip	$T_C = 25^\circ\text{C}$		0.7		m Ω
		$T_C = 125^\circ\text{C}$		1		m Ω
$R_{th(c-s)}$	per module			0.04		K/W
M_s	to heat sink (M5)		3		5	Nm
M_t	to terminals (M6)		2.5		5	Nm
w					350	g
Temperatur Sensor						
R_{100}	$T_C=100^\circ\text{C}$ ($R_{25}=5\text{ k}\Omega$)			$493 \pm 5\%$		Ω
$B_{100/125}$	$R_{(T)}=R_{100}\exp[B_{100/125}(1/T-1/T_{100})]$; $T[\text{K}]$;			3550 $\pm 2\%$		K



GD

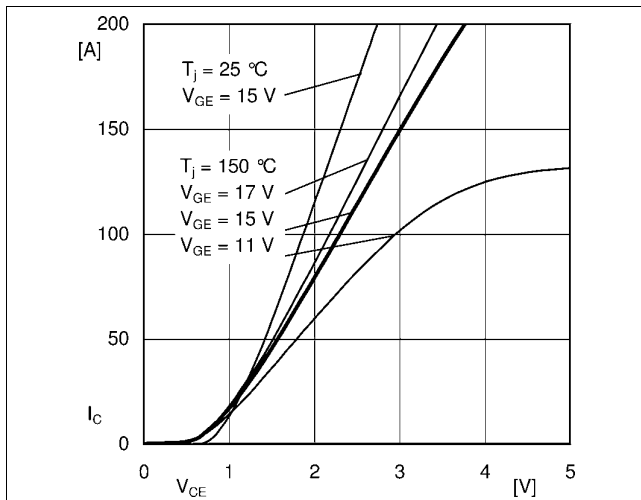


Fig. 1: Typ. output characteristic, inclusive $R_{CC+EE'}$

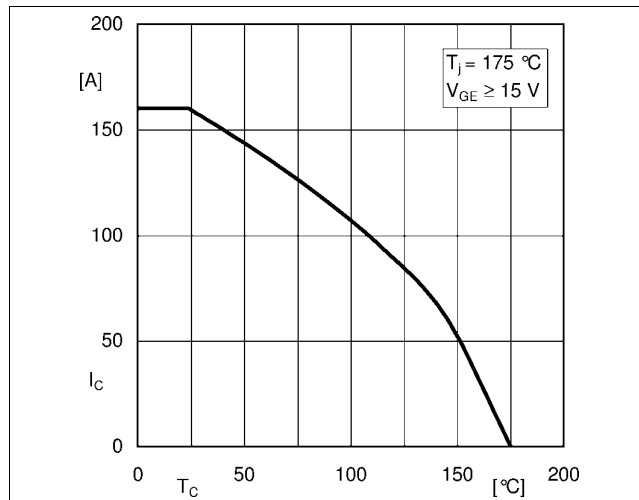


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

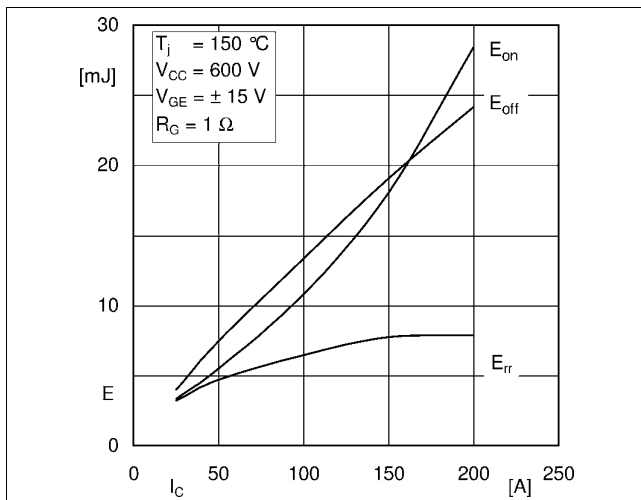


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

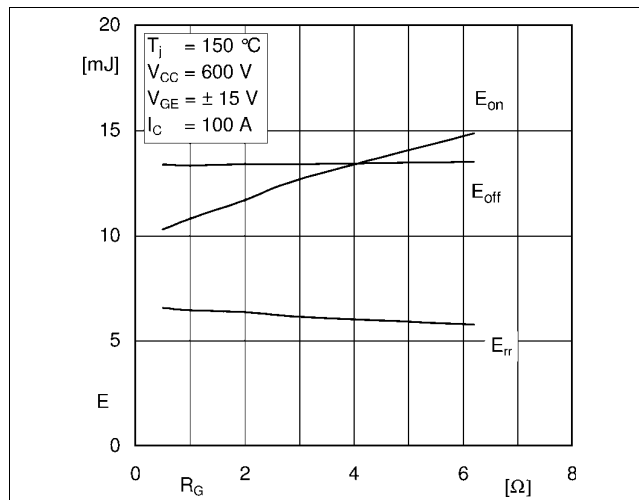


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

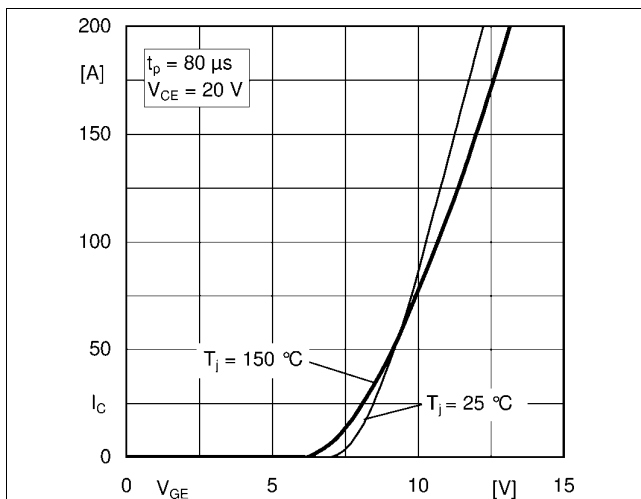


Fig. 5: Typ. transfer characteristic

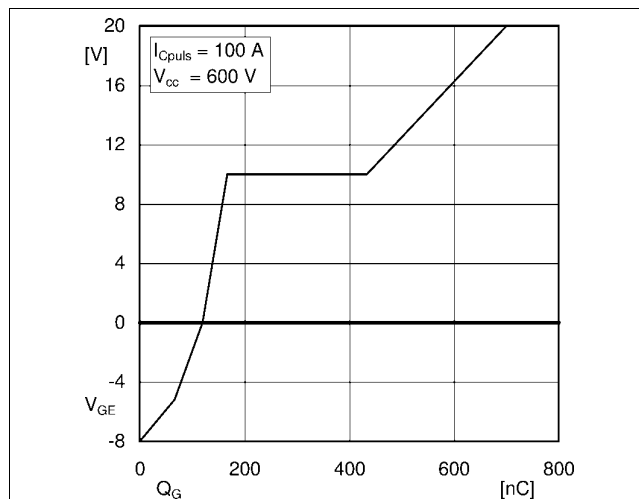


Fig. 6: Typ. gate charge characteristic

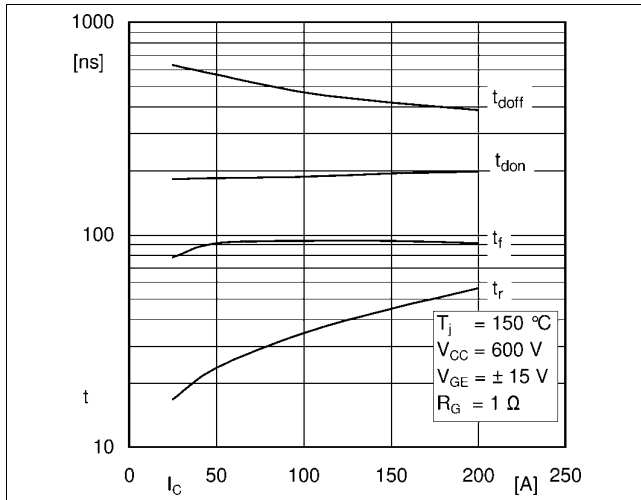


Fig. 7: Typ. switching times vs. I_C

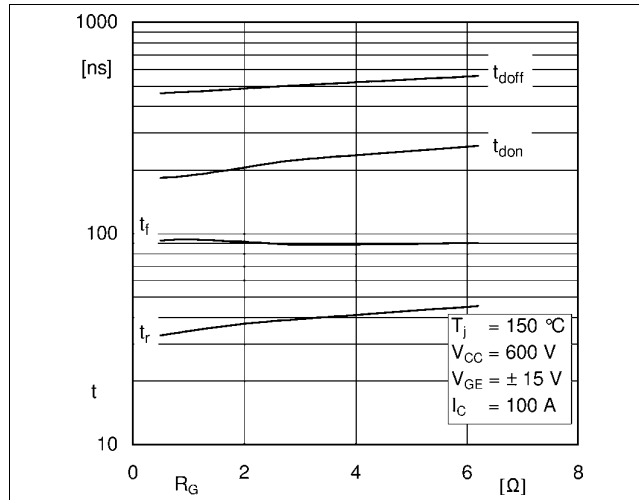


Fig. 8: Typ. switching times vs. gate resistor R_G

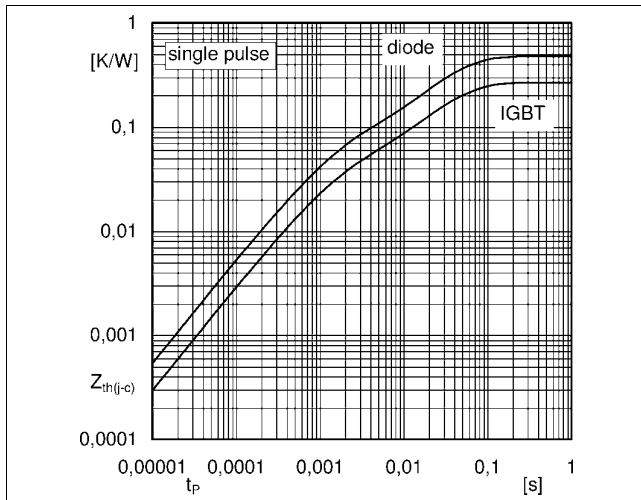


Fig. 9: Typ. transient thermal impedance

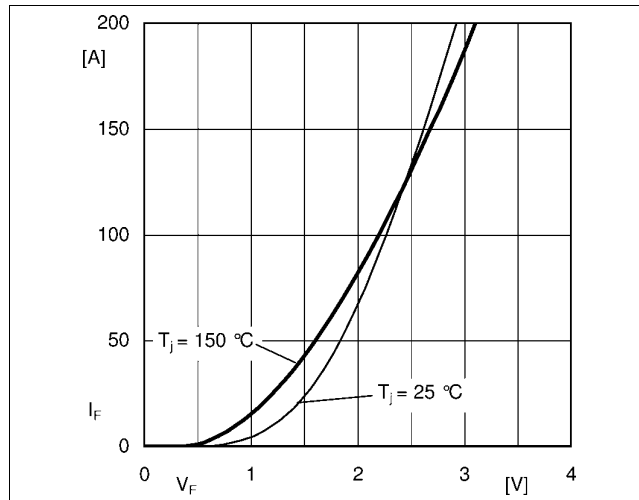


Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC'+EE'}$

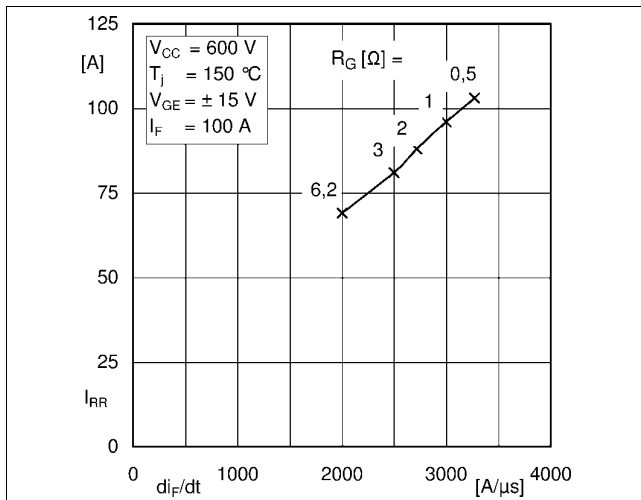


Fig. 11: Typ. CAL diode peak reverse recovery current

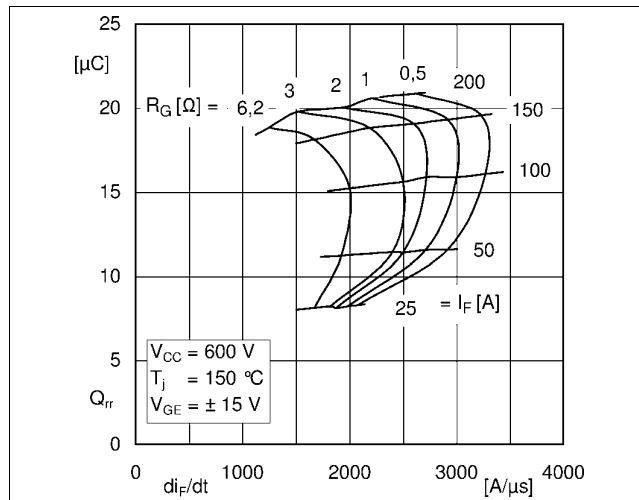
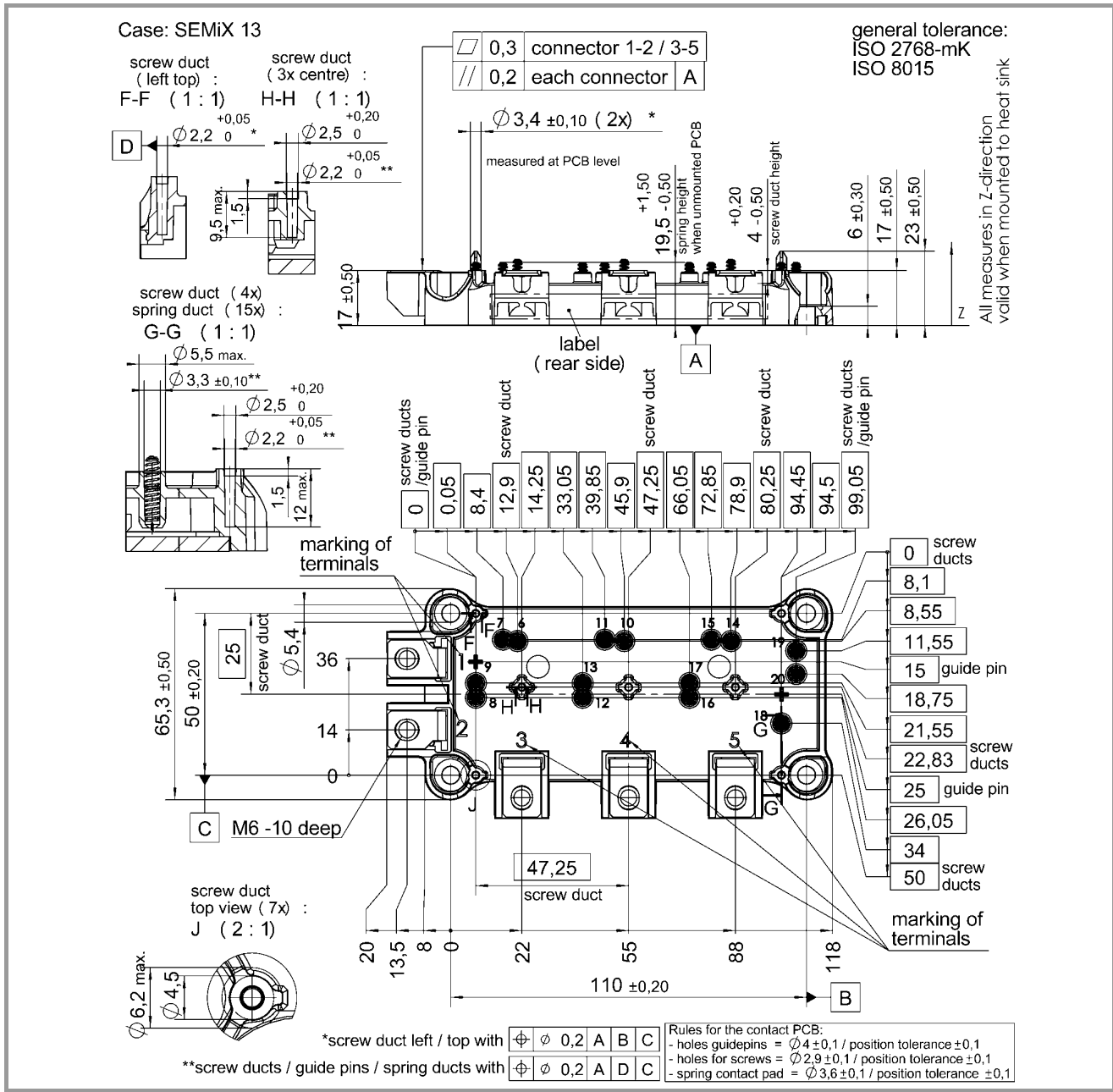
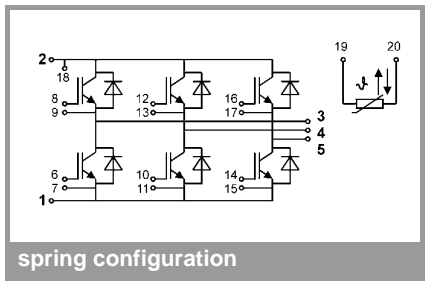


Fig. 12: Typ. CAL diode recovery charge

SEMiX101GD12E4s



SEMiX 13



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.